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**200°C OPERATION OF A DC-DC  
CONVERTER WITH SiC POWER  
DEVICES (PREPRINT)**

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# 200°C Operation of a DC-DC Converter with SiC Power Devices

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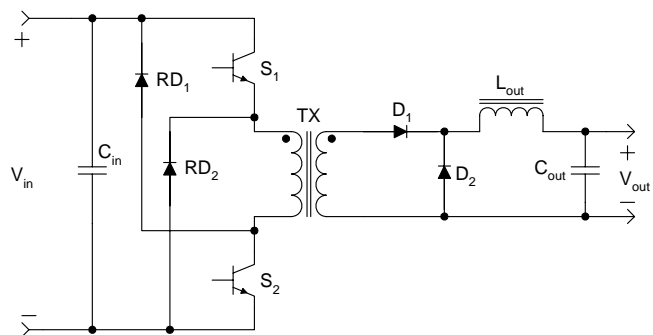
## I. INTRODUCTION

High temperature electronics is becoming increasingly important in a multitude of applications [1] including automobiles (on-engine and in-transmission environments), well drilling (instrumentation for oil and gas recovery), and aircraft and spacecraft (turbine engines, motor drives, space propulsion systems). Advances in silicon-on-insulator (SOI) technology and the steady development of wider band semiconductors such as silicon carbide (SiC) are enabling the practical deployment of high temperature electronics in the near future. As temperature increases in a semiconductor, intrinsic carrier density increases thereby increasing the leakage current. Additionally, device parameters vary, electromigration of interconnection traces increase, dielectric breakdown strength decreases, and TCE mismatches stress the die mechanically. Even with the use of SOI technology [2,3], these effects limit the maximum ambient use temperature of Si power devices to 200°C. Above 200°C, use of wider bandgap semiconductor materials become imperative [4,5] since they produce a smaller concentration of intrinsic carriers than Si at elevated temperatures. Among the wide bandgap materials, SiC technology is far ahead of GaN and diamond technologies. SiC Schottkys are commercially available, and the use of SiC BJTs, JFETs, and MOSFETs has been reported at the developmental level. In the passive components domain, high temperature ferrite magnetic material has been developed recently, [6,7] and the development of high temperature high frequency capacitors with acceptable drop in capacitance value and decrease in leakage currents is in progress [8]. Previous studies [9-12] have reported high temperature operation of SiC diodes, JFETs, and MOSFETs as well as power converters utilizing these devices. This paper presents the operation of a 180 W, 270 V/28 V, 100 kHz two-transistor forward dc-dc converter at elevated

temperatures up to 200°C, utilizing SiC power devices and high temperature magnetics.

## II. DESIGN OF THE POWER CONVERTER

A 180 W, 270 V/28 V, 100 kHz two-transistor forward converter was designed to operate with a minimum load power of 15 W under continuous conduction mode and a peak-to-peak output ripple of 140 mV (i.e., 0.5% of the output voltage). The two-transistor forward converter [13] power stage is shown in Figure 1. This converter goes through three different modes of operation within a switching cycle: energy transfer mode ( $S_1$  and  $S_2$  are on, and  $D_1$  conducts), transformer reset mode ( $RD_1$  and  $RD_2$  conduct applying reverse input voltage to the transformer winding, and output inductor current freewheels through  $D_2$ ), and dead time mode (all primary switches are off while the output inductor current is freewheeling through  $D_2$ ). Because of the way the transformer core reset is achieved, the maximum duty cycle is limited to 0.5. For this design, a maximum duty cycle of 0.45 is used. Key advantages of this topology are: transformer leakage inductance energy is fed back to the input capacitor via  $RD_1$  and  $RD_2$ , and maximum voltage stress on the primary switches is limited to the input voltage level requiring no primary-side snubber circuits. Additionally, voltage shoot-through is absent in this topology since  $S_1$  and  $S_2$  are turned on and off at the same time.



**Figure 1:** Power stage of the two-transistor forward dc-dc converter.

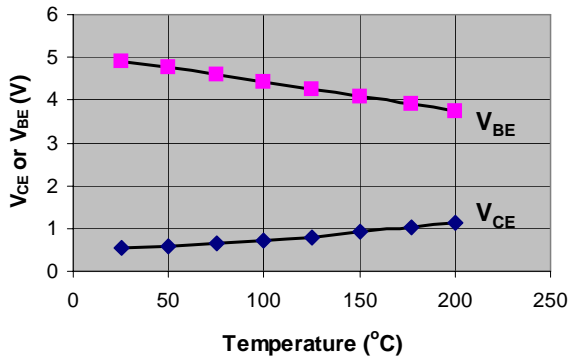
### A. SiC power semiconductor selection

The power semiconductors used in the power stage design are shown in the table below. All three devices are from Cree Incorporated.

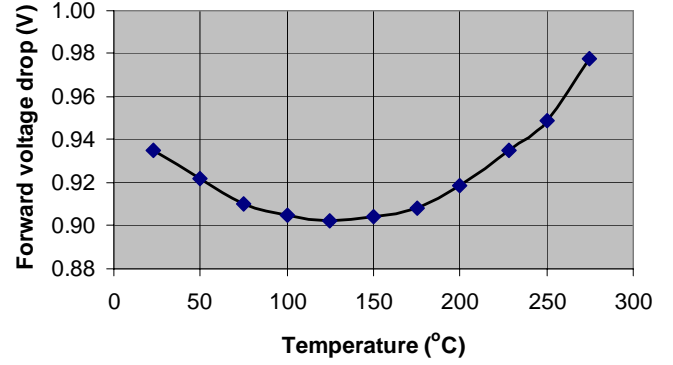
Device ref. designator	Device type	Part #	Key specifications
S <sub>1</sub> , S <sub>2</sub>	BJT	---	1000 V, 5 A, T <sub>j,max</sub> >300°C, TO-257
RD <sub>1</sub> , RD <sub>2</sub>	Schottky	CSD10060	600V, 10 A, V <sub>F</sub> =2.0 V @ 10 A, T <sub>j</sub> = 175°C, TO-220
D <sub>1</sub> , D <sub>2</sub>	Schottky	CSD20030	300V, 20 A, V <sub>F</sub> =1.4 V @ 10 A, T <sub>j</sub> = 175°C, TO-247

Development of 4H-SiC BJTs with high dc current gain and associated high temperature current-voltage characteristics have been recently reported [14]. These 1000 V/30 A devices with an active area of 3×3 mm<sup>2</sup> show fast switching properties and a sharp avalanche behavior at a collector-emitter voltage of 1000 V. The dc characteristics of these devices at room temperature include a forward voltage drop of 2 V at 30 A of collector current with a current gain of 40 representing a current density of 333 A/cm<sup>2</sup>. The reported dc current gain for these devices is 30 at 275°C.

The switching devices used in the two-transistor forward power converter implementation are from the same family of devices reported in [14], and are currently not available commercially. SiC Schottky rectifiers, however, are commercially available with 600 and 1200 V blocking voltage ratings and current handling capabilities of up to 20 A. The positive temperature coefficient of V<sub>F</sub> makes these devices very amenable to paralleling in order to achieve high current handling capability. Figure 2 below shows the V<sub>BE</sub> and V<sub>CE</sub> variation with temperature for the BJT used in the design, and Figure 3 shows the forward voltage drop variation of the 300 V Schottky used in the output rectifier design.



**Figure 2:** SiC BJT junction voltages for a dc current gain of 10 (I<sub>B</sub> = 0.2 A; I<sub>C</sub>=2 A).



**Figure 3:** SiC Schottky diode (CSD20030) forward voltage drop for a dc forward current of 6.5 A.

### B. Transformer design

A planar core of E46410 configuration made of Fe-Mn-Zn ferrite material with a Curie temperature in excess of 300°C [6,7] was used in designing the transformer. Key magnetic properties of this high temperature material are: relative permeability of 500-1000 at 25°C, saturation flux density of 0.48 T at 25°C/0.3 T at 200°C/0.1 T at 300°C, coercive force of 0.5 Oe at 25°C and 0.35 Oe at 200°C, power loss of less than 1 W/cc @200 kHz/0.08 T, and a resistivity of 100-200 Ω-cm.

For this design, the turns ratio (primary-to-secondary) was calculated using (1)

$$TX\_ratio = \frac{V_{in,min} D_{max}}{V_{out}} \quad (1)$$

where,  $V_{in,min}$  is 250 V,  $D_{max}$  is 0.45, and  $V_{out}$  = 28 V.

The transformer turns ratio used in the design is 3.5 to account for converter losses. The primary number of turns was calculated using (2)

$$N_p = \frac{V_{in,min} D_{max}}{f_s A_e B_{max}} \quad (2)$$

where,  $V_{in,min}$  is 250 V,  $D_{max}$  is 0.45,  $f_s$  is 100 kHz,  $A_e$  is 516×10<sup>-6</sup> m<sup>2</sup>, and  $B_{max}$  is 0.08 T.

Based on above calculations, the transformer was designed with 28 turns in the primary and 8 turns in the secondary. The design assumed a peak flux density of 0.08 T in order to avoid magnetic saturation of the core for up to 300°C. The primary winding used one strand of #24 copper wire with Fluorene Polyester (FPE) coated insulation. The breakdown strength of FPE is approximately 10 kV/mil for up to 300°C. The secondary winding was implemented with one strand of 0.3125"x0.003" copper foil using Kapton polyimide film tape as the insulating material (rated for operation up to 260°C).

### C. Output inductor design

The E46410-shaped high temperature core was also used in designing the inductor. Based on the minimum load

current requirement of 0.62 A, a minimum duty ratio of 0.34, an output voltage of 28 V, and a switching frequency of 100 kHz, the required value of 150  $\mu\text{H}$  for the output filter inductance was calculated using (3).

$$L_{out} = \frac{V_{out}(1 - D_{min})}{2f_s I_{o,min}} \quad (3)$$

The required air gap of 1.8 mm (70 mils) in the center leg of the core was calculated using (4) for energy storage purpose. The values used to calculate the air gap length are:  $\mu_0 = 4\pi \times 10^{-7} \text{ T}\cdot\text{m/A}$ ,  $L_{out} = 150 \mu\text{H}$ ,  $I_{o,max} = 7 \text{ A}$ ,  $B_{max} = 0.1 \text{ T}$ , and  $A_e = 516 \times 10^{-6} \text{ m}^2$ .

$$l_g = \frac{\mu_0 L_{out} I_{o,max}^2}{B_{max}^2 A_e} \quad (4)$$

A peak flux density of 0.1 T was used in the design with a peak-to-peak ac flux density of only 15 mT in order to guarantee 200°C operation of the inductor. In winding the output filter inductor, 24 turns of six strands of FPE-coated #24 wire were used.

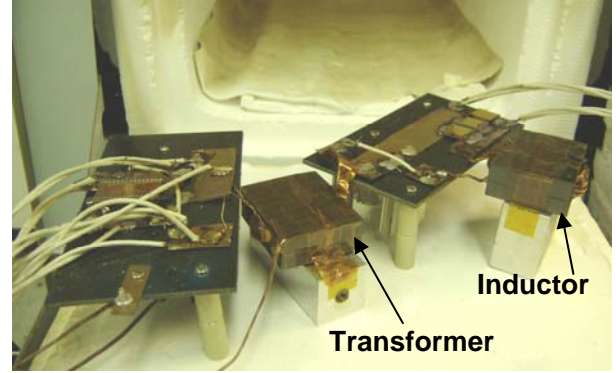
#### D. Capacitor selection

For higher dielectric constant capacitors such as ceramics, capacitance generally decreases and leakage current increases with increasing temperatures [8]. For low capacitance values, C0G (Class I) ceramic capacitors are likely the best choice due to lower dissipation factor and stable temperature characteristics. However, due to the need of capacitance in the range of 10-30  $\mu\text{F}$  for this power converter design, X7R (Class II) ceramic capacitors are the next best alternative. For this design, the input filter capacitance of 10  $\mu\text{F}$  consisted of two 5  $\mu\text{F}/300\text{V}/\text{X7R}$  (AVX) capacitors. The output filter capacitance of 45  $\mu\text{F}$ , however, consisted of three 15  $\mu\text{F}/25\text{V}$  Class-II high temperature (200°C) capacitors from Novacap. It shall be noted that the capacitance of high temperature capacitors from Novacap drops significantly in value between 150°C and 200°C.

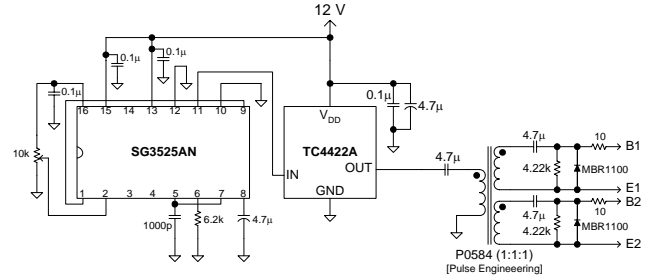
### III. EXPERIMENTAL SETUP AND TESTING

Power stage of the converter was built using two pieces of FR-4 board and 5 mils copper strips, high temperature wire (260°C; MIL-W-25038/1), and high temperature solder (240°C liquidus temperature; 95Sn/5Sb). Figure 4 shows a pictorial view of the power stage of the converter placed outside the oven. The power semiconductor devices are located on the bottom side of FR-4 boards. The complete power stage was placed inside an oven with the control board placed outside. This necessitated long wires out of the oven to be able to feed base-emitter signals to the BJTs. The control circuit used to drive the BJTs is shown in Figure 5. Additionally, long wires out of the oven were

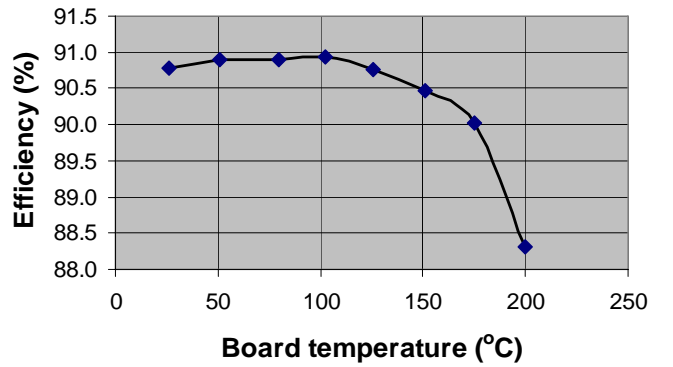
needed for connecting to the input source and output load, and for monitoring voltages at various points of the converter. The converter was tested for ambient (board) temperatures of 25°C to 200°C, in steps of approximately 25°C. The measured power stage efficiency of the converter, shown in Figure 6, remained between 90% and 91% in the 25°C to 175°C range. However, the converter efficiency dropped from 90% at 175°C to 88.3% at 200°C.



**Figure 4:** Pictorial view of the converter power stage (outside the oven).



**Figure 5:** Control circuit used to drive the SiC BJTs.

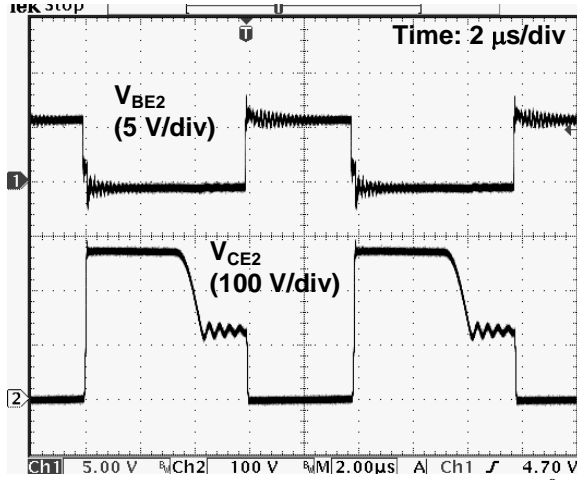


**Figure 6:** Efficiency of the converter as a function of temperature ( $P_{out} = 180 \text{ W}$ ).

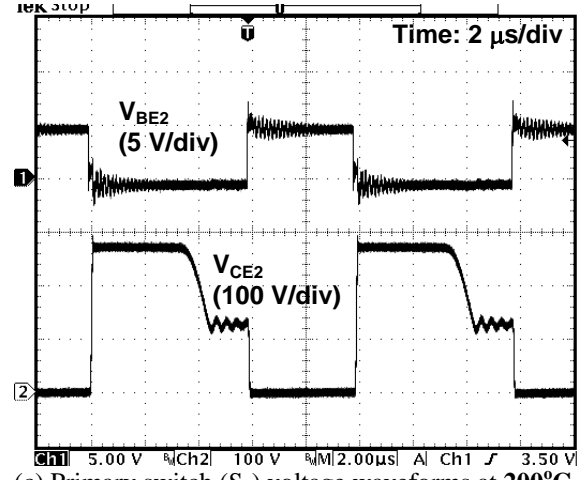
Figure 7 in the next page shows the base-emitter and collector-emitter voltages of the primary switch ( $S_2$ ), output diode ( $D_2$ ) voltage, and transformer (TX) primary voltage waveforms at 26°C and 200°C. The  $V_{BE2}$  waveform looks noisy primarily due to lead inductance of long wires used to

connect the control board outside the oven to the BJT inside the oven. The  $V_{D2}$  waveform shows the high frequency ringing at primary switch turn-on due to resonance between the transformer leakage inductance and the output diode junction capacitance. This ringing can be reduced significantly by the use of a snubber circuit in the secondary side of the converter. The  $V_{XFMR,PRI}$  waveform clearly shows the complete demagnetization of the core and the

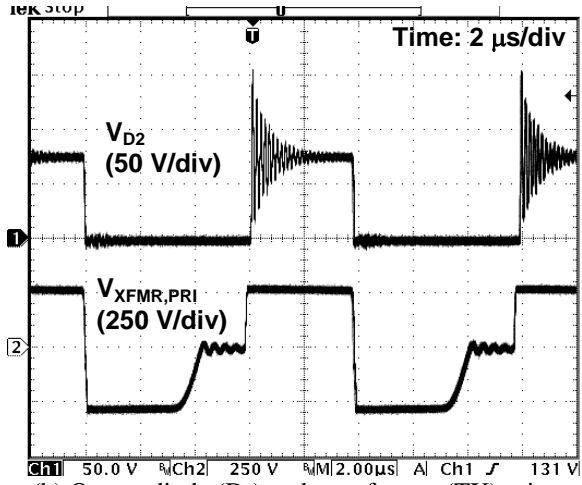
associated dead time. Most importantly, it shall be observed that the waveforms shown in Figure 7 clearly demonstrate that the operation of BJTs, Schottkys, and the transformer are practically unchanged over the wide temperature range of 26°C to 200°C. This led to testing the converter in excess of 200°C. However, the converter failed shorted at 215°C.



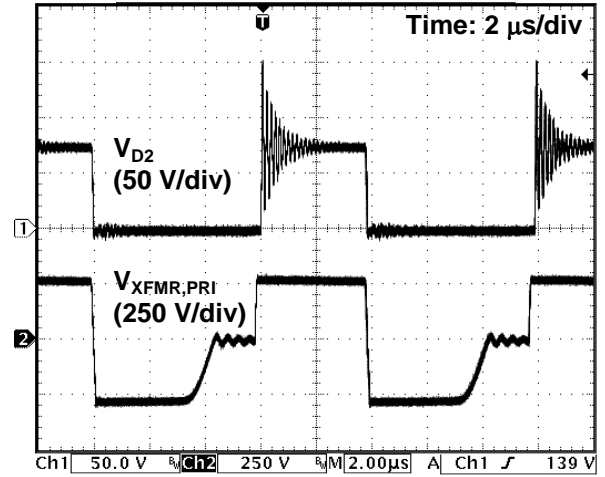
(a) Primary switch ( $S_2$ ) voltage waveforms at 26°C



(c) Primary switch ( $S_2$ ) voltage waveforms at 200°C



(b) Output diode ( $D_2$ ) and transformer (TX) primary voltage waveforms at 26°C



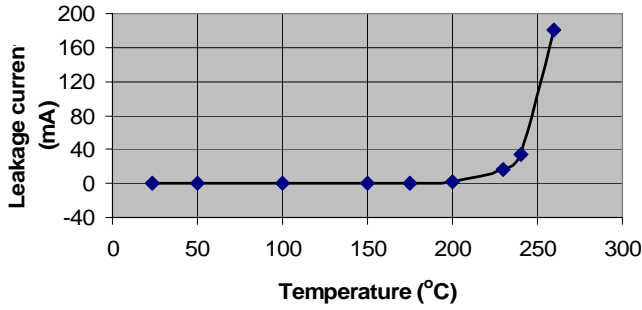
(d) Output diode ( $D_2$ ) and transformer (TX) primary voltage waveforms at 200°C

**Figure 7:** Power converter voltage waveforms under full load at 26°C (left) and 200°C (right).

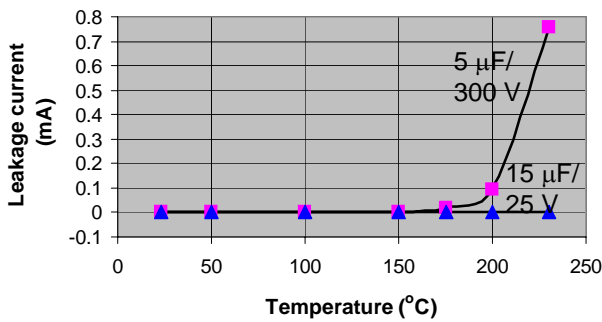
Upon removing the converter from the oven, it was noticed that the input capacitor (2\*5  $\mu$ F/300V; X7R) cracked; and the power converter ran successfully once the cracked input capacitor was removed. Further testing of this capacitor revealed the fact that the converter failed shorted due to shorting of this capacitor (contributed by excessive leakage current and self-heating/thermal runaway). This led to testing of various X7R and Class-II capacitors for leakage current over temperature under dc condition. Figure 8 shows that leakage current of X7R capacitors (30  $\mu$ F/300V

and 5  $\mu$ F/300 V) starts to increase exponentially above 175°C. The 5  $\mu$ F/300V capacitor (used in the power converter design) seems usable to approximately 200°C; however, its reliability will definitely be questionable under ac ripple current excitation. The high temperature Class-II capacitor (15  $\mu$ F/25 V from Novacap) shows almost no increase in leakage current up to 225°C, and is definitely usable for 200°C design. A pictorial view of the high temperature cracking of X7R capacitors is shown in Figure 9. This experimental study does explain the failure of the

power converter at 215°C due to a short created by the leaking X7R input capacitor and the significant decrease in converter efficiency from 175°C to 200°C.

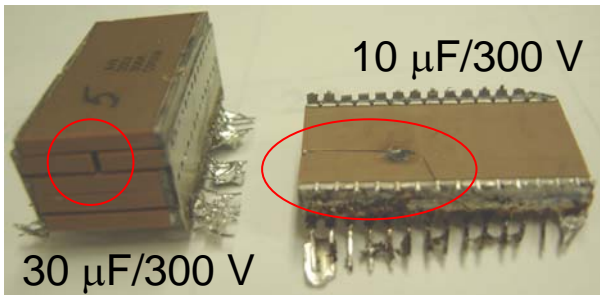


(a) 30 µF/300 V ceramic (X7R) capacitor



(b) 5 µF/300 V ceramic (X7R) and 15 µF/25 V ceramic (Class-II) capacitors

**Figure 8:** Measured leakage current of ceramic capacitors as a function of temperature.



**Figure 9:** Pictorial view of the high temperature cracking of X7R capacitors.

#### IV. SUMMARY AND FUTURE WORK

Successful operation of the power converter at elevated temperatures up to 200°C has been reported. Replacing the 300 V/X7R input capacitor with high temperature Class-II or C0G ceramic capacitor would likely permit the operation of the converter to at least 250°C, and this change will be incorporated in the next design update. Implementation of a

higher power version (e.g., 1 kW) of the converter using a full-bridge topology is under consideration now. The use of SiC JFETs and MOSFETs as power switch, in place of SiC BJTs, will be studied in the near future as well.

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